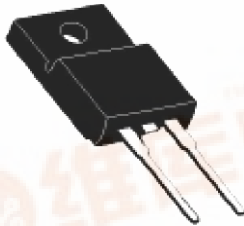




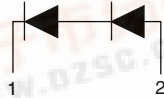
8S2TH06FP

Vishay High Power Products

Hyperfast Rectifier, 8 A FRED Pt™



2L TO-220 FULL-PAK



FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Designed and qualified for industrial level



RoHS
COMPLIANT

DESCRIPTION

8S2TH06FP 600 V series are the state of the art tandem hyperfast recovery rectifiers: excellent switching performance and extremely low forward voltage drop trade off is overcome, boosting overall application performance.

Specially designed for CCM PFC application, these devices show incomparable performance in every current intensive hard switching application.

Optimized reverse recovery stored charge enables downsizing of boosting switch and cooling system, increased operating frequency make possible use of smaller reactive elements. Cost effective PFC application is then possible with high efficiency over wide input voltage range and loading factor.

Plastic insulated package features easy mounting together with not insulated parts.

PRODUCT SUMMARY

t_{rr}	19 ns
$I_{F(AV)}$	8 A
V_R	600 V

ABSOLUTE MAXIMUM RATINGS FOR BOTH DIODES

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Repetitive peak reverse voltage	V_{RRM}		600	V
DC forward current	I_F	50 % duty cycle, rect. waveforms, $T_C = 93\text{ °C}$	8	A
Non-repetitive peak surge current	I_{FSM}	$T_C = 25\text{ °C}$	100	
Operating junction and storage temperatures	T_J, T_{Stg}		- 55 to 175	°C

ELECTRICAL SPECIFICATIONS FOR BOTH DIODES ($T_J = 25\text{ °C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR}, V_R	$I_R = 100\text{ }\mu\text{A}$	600	-	-	V
Forward voltage	V_F	$I_F = 8\text{ A}$	-	2.1	2.4	
		$I_F = 8\text{ A}, T_J = 125\text{ °C}$	-	1.7	2	
		$I_F = 8\text{ A}, T_J = 150\text{ °C}$	-	1.6	1.8	
Reverse leakage current	I_R	$V_R = V_R\text{ rated}$	-	< 1	10	μA
		$T_J = 125\text{ °C}, V_R = V_R\text{ rated}$	-	7	80	
		$T_J = 150\text{ °C}, V_R = V_R\text{ rated}$	-	27	100	
Junction capacitance	C_T	$V_R = 600\text{ V}$	-	12	-	pF



New Product

8S2TH06FP



Vishay High Power Products

Hyperfast Rectifier,
8 A FRED Pt™

DYNAMIC RECOVERY CHARACTERISTICS FOR BOTH DIODES ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Reverse recovery time	t_{rr}	$I_F = 1.0\text{ A}$, $di_F/dt = -50\text{ A}/\mu\text{s}$, $V_R = 30\text{ V}$	-	-	25	ns
		$T_J = 25\text{ }^\circ\text{C}$	-	19	-	
		$T_J = 125\text{ }^\circ\text{C}$	-	35	-	
Peak recovery current	I_{RRM}	$T_J = 25\text{ }^\circ\text{C}$	-	2.8	-	A
		$T_J = 125\text{ }^\circ\text{C}$	-	4.6	5.5	
Reverse recovery charge	Q_{rr}	$T_J = 25\text{ }^\circ\text{C}$	-	26	-	nC
		$T_J = 125\text{ }^\circ\text{C}$	-	84	-	

THERMAL - MECHANICAL SPECIFICATIONS FOR BOTH DIODES						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T_J, T_{Stg}		-55	-	175	$^\circ\text{C}$
Thermal resistance, junction to case	R_{thJC}		-	4.1	4.8	$^\circ\text{C}/\text{W}$
Thermal resistance, case to heatsink	R_{thCS}	Mounting surface, flat, smooth and greased	-	0.2	-	
Weight			-	2.0	-	g
			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style 2L TO-220 FULL-PAK	8S2TH06FP			



New Product

8S2TH06FP

Hyperfast Rectifier,
8 A FRED Pt™

Vishay High Power Products

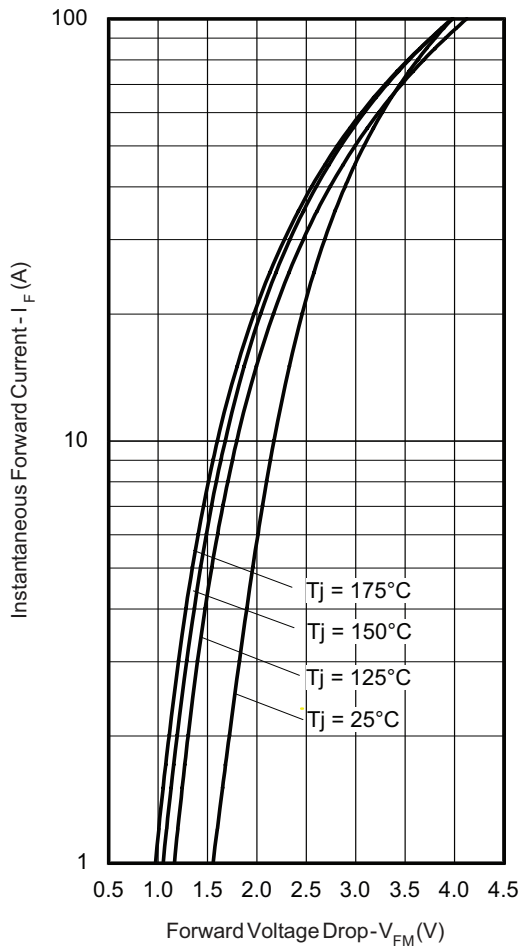


Fig. 1 - Maximum Forward Voltage Drop Characteristics

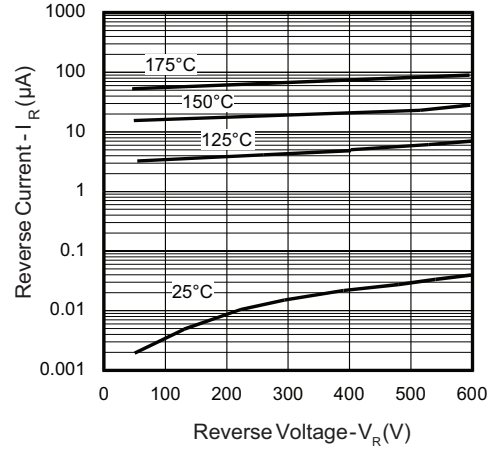


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

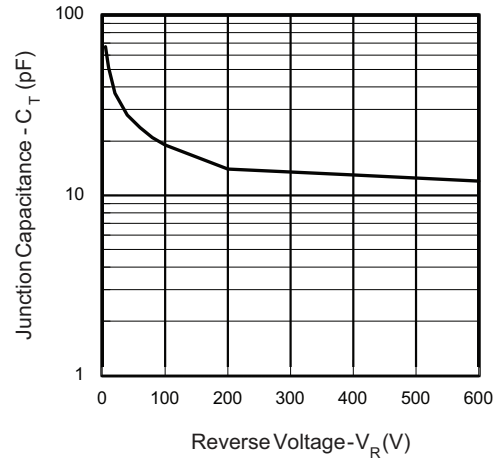


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

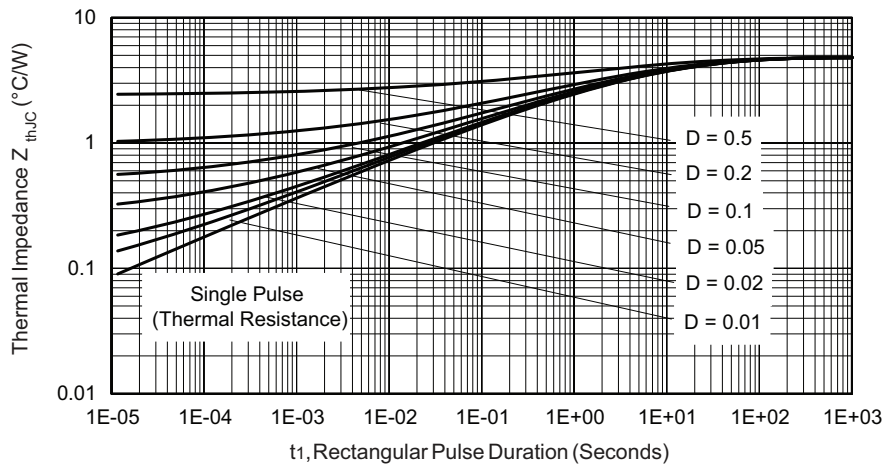


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

8S2TH06FP



Vishay High Power Products

Hyperfast Rectifier,
8 A FRED Pt™

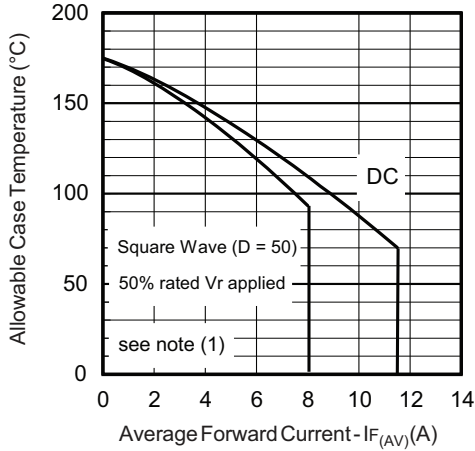


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

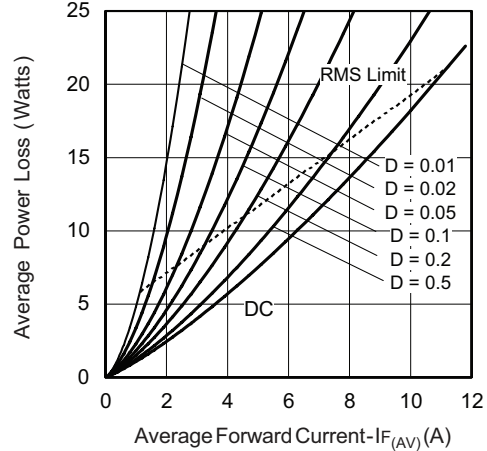


Fig. 6 - Forward Power Loss Characteristics

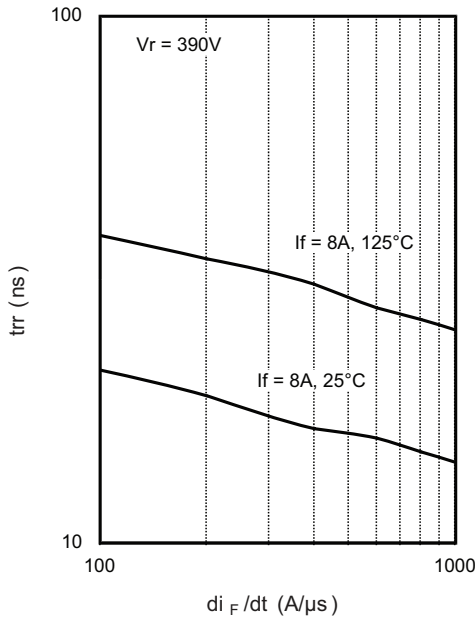


Fig. 7 - Typical Reverse Recovery Time vs. di_F/dt

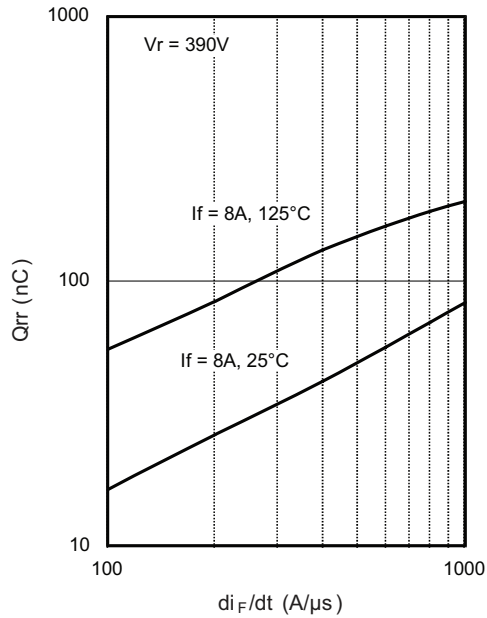


Fig. 8 - Typical Stored Charge vs. di_F/dt

Note

- (1) Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;
- Pd = Forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6);
- Pd_{REV} = Inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at $V_{R1} = 50\%$ rated V_R

LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95263
Part marking information	http://www.vishay.com/doc?95265



Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.